

Substitute for form 1449A/PTO			Complete (if Known)	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/642,305
Sheet	1	of	Filing Date	August 18, 2003
		7	Firm Named Inventor	Hongyong ZHANG et al.
			Art Unit	2811
			Examiner Name	D. Owens
			Attorney Docket Number	740756-2646

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No.	U.S. Patent Document Number - Kind Code ¹ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, or References in Fig.	See Lines, Where pages or References to Appear
D/O		US-4,680,609	07/14/1987	Calder et al.		
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		US-4,459,739	07/17/1984	Shepherd et al.		

Examiner Signature	Douglas W. Owens	Date Considered	11/16/04
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Examiner Name	D. Owens			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Chp No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patent or Application of Claim Document	Page, Column, Line, Where Relevant Passages or Relevant Figures Appear	Type
		Country Code ²	Number ³				
2/12/04		JP	62-211165	09/1987			Abstract
		JP	02-77127	03/16/1990			Abstract
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		JP	60-043869	01/08/1985			Abstract
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		JP	01-209764	08/23/1989	Kato		Ex. Cited
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		JP	62-244165	10/24/1987			Abstract
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		JP	63-036574	02/17/1988	Konishi et al.		Abstract
2/12/04		JP	55-163848	12/20/1980			Full

Examiner Signature	<i>Douglas K. Owens</i>	Date Considered	11/10/04
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				Art Unit	2811
				Examiner Name	D. Owens
Sheet	4	of	7	Attorney Docket Number	740756-2646

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issu number(s), publisher, city and/or country where published.
21/2		T. TAKESHITA et al., "Study of ECR Hydrogen Plasma Treatment on Poly-Si Thin Film Transistors" Japanese Journal of Applied Physics, Vol. 27, No. 11, November 1988, pp. L2118-L2120, Tokyo, JP.
		S. Wolf & R.N. Tauber, "Silicon Processing of the VLSI ERA", Lattice Press, 1286, pp. 168-199, 334-335, Vol. I.
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		D.L. Crosthwait, et al., LASER AND E-BEAM SOLID INTERACTIONS, PROC. MRJ 1980, P.399, "...LASER IRRADIATION THERMAL OXIDES...".
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		S. Suyama et al., IEEE Trans. Electron Dev., 34(10) (1987) 2124, "...MOSFET's Utilizing Oxygen-Argon Sputter-Deposited Gate Oxide Films", October, 1987.
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		Katoda, "Estimation of a Semiconductor by a Laser Raman Spectroscopy", Published by Tokyo University, 1988, pp. 67-75 (in Japanese with Concise English Statement).
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Examiner Signature	<i>D. Owens</i>	Date Considered	11/10/04
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Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark		Attorney Docket: 740736-2646		Sheet 6 of 7 Serial No. 10/642,305		
INFORMATION DISCLOSURE STATEMENT								
(Use several sheets if necessary)								
				Applicant: Hongyong ZHANG et al.				
				Filing Date: August 18, 2003		Group: 2811		
U.S. PATENT DOCUMENTS								
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)		
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	4,619,034	10/28/86	Janning					
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Examiner <i>DWO</i>	Date Considered <i>11/10/04</i>							
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Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket: 740756-
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Serial No. 10/642,305

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	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<i>20/09</i>	57-109377	07/07/82	Japan			Abstract	
	58-002073	01/07/83	Japan			Full	
	58-182816	10/25/83	Japan			Abstract	
	59-040580	03/06/84	Japan			Abstract	
	59-108360	06/22/84	Japan			Abstract	
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	2 087 147 A	05/19/82	Great Britain			Full	

Examiner

Ralph W. Owe

Date Considered

11/10/04

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